

GaAlAs Infrared Emitter

OPE5194WK

The **OPE5194WK** is GaAlAs infrared emitting diode that is designed for high radiant intensity and low forward voltage. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has narrow beam angle with lensed package and cup frame.

FEATURES

- High-output power
- Narrow beam angle
- Available for pulse operating

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

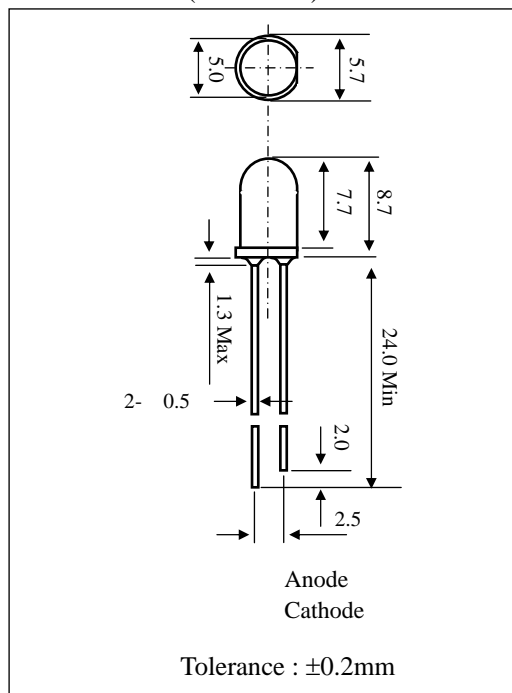
STORAGE

- Condition : 5°C~35°C,R.H.60%
- Terms : within 3 months from production date
- Remark : Once the package is opened, the products should be used within a day.

Otherwise, it should be keeping in a damp proof box with desiccants.

* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

DIMENSIONS (Unit : mm)



MAXIMUM RATINGS

(Ta=25°C)

| Item | Symbol | Rating | Unit |
|-------------------------------------|----------|----------|------|
| Power Dissipation | P_D | 150 | mW |
| Forward current | I_F | 100 | mA |
| Pulse forward current ^{*1} | I_{FP} | 1.0 | A |
| Reverse voltage | V_R | 5.0 | V |
| Operating temp. | Topr. | -25~ +85 | °C |
| Soldering temp. ^{*2} | Tsol. | 260. | °C |

^{*1}.Duty ratio = 1/100, pulse width=0.1ms.

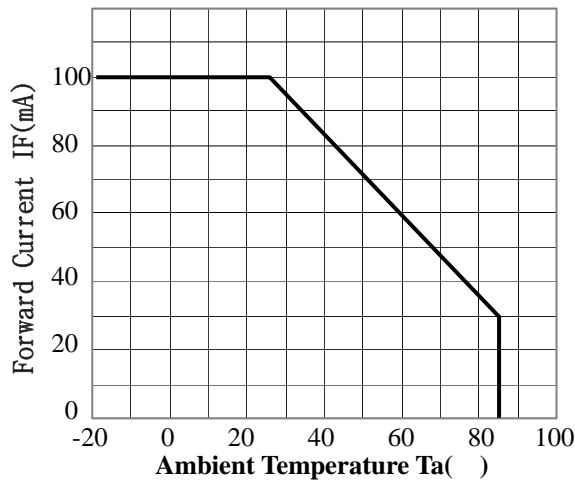
^{*2}.Lead Soldering Temperature (2mm from case for 5sec.).

ELECTRO-OPTICAL CHARACTERISTICS

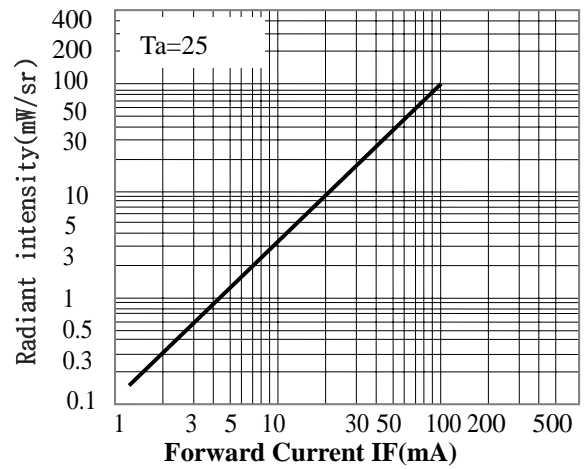
(Ta=25°C)

| Item | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|--------------------------|-------------|--------------------|------|------|------|---------------|
| Forward voltage | V_F | $I_F=100\text{mA}$ | | 1.4 | 1.7 | V |
| Reverse current | I_R | $V_R=5\text{V}$ | | | 10 | μA |
| Capacitance | C_t | $f=1\text{MHz}$ | | 20 | | pF |
| Radiant intensity | I_e | $I_F=100\text{mA}$ | | 100 | | mW/sr |
| Peak emission wavelength | λ_p | $I_F=50\text{mA}$ | | 940 | | nm |
| Spectral bandwidth 50% | | $I_F=50\text{mA}$ | | 45 | | nm |
| Half angle | | $I_F=100\text{mA}$ | | ±10 | | deg. |

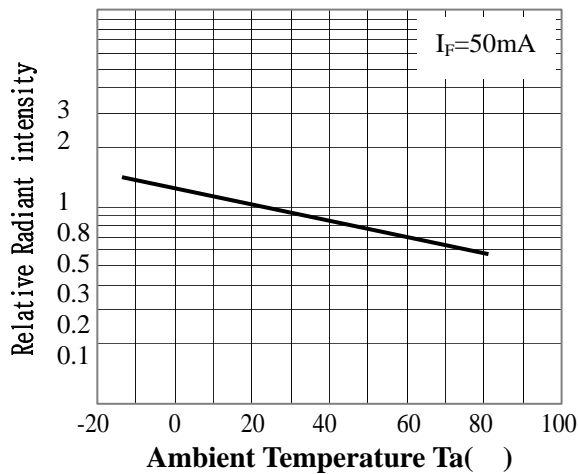
- **FORWARD CURRENT Vs. AMBIENT TEMP.**



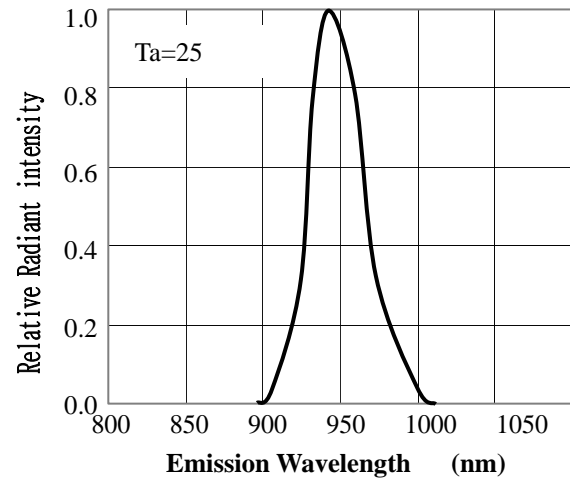
- **RADIANT INTENSITY Vs. FORWARD CURRENT.**



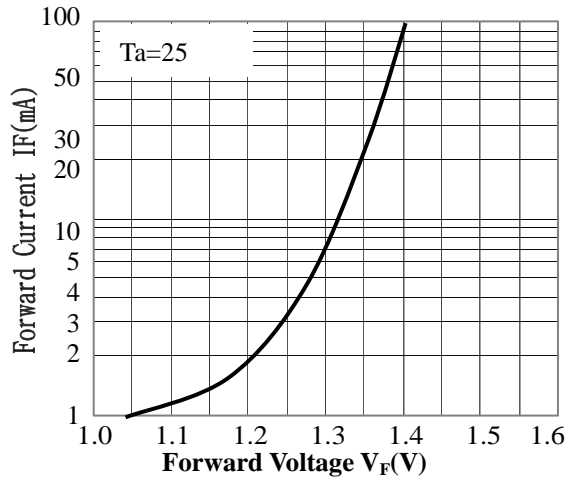
- **RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.**



- **RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.**



- **FORWARD CURRENT Vs. FORWARD VOLTAGE**



- **ANGULAR DISPLACEMENT Vs. RELATIVE RADIANT INTENSITY**

